

Electronic Materials



New Generation Via Fill Technology for HDI Application

Dow Electronic Materials R&D Process Technology

Dow.com

Agenda

Introduction

- Surface Appearance, Via Filling and Through Hole TP% Performance
- > Mass Production Status and Deposit Physical Properties
- > Summary
- > Q & A



Technology Trend on HDI



- HDI-board is required to perform higher reliability, finer traces, smaller via holes, multilayers and higher densities
- Key challenge: Electrical performance, Low cost, High density



Microvia Filling Mechanism



- Additives used for bright acid copper plating are divided into 3 categories:
 - (1) Carrier: make deposit a tighter grain structure, improve plating distribution & TP.
 - (2) Brightener: direct enhance physical properties of the deposit, ex: tensile strength & elongation.
 - (3) Leveler: adsorb preferentially at high points in the plating topography, allow low currentdensity areas to catch up with high area.



Why This Product Produce ?

Good Surface Appearance

Good Blind Via Filling Performance

No Bump Issue

Good Through Hole TP% and Knee TP% performance



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Surface Appearance Performance Compared with Conventional Product

Product	New Generation	Conventional
Haring Cell		
Mass Production		

Parameter	Value
CuSO ₄ •5H ₂ O	230g/L
H ₂ SO ₄	60g/l
Chloride	50ppm
Current density	15 ASF
Temperature	23°C



Via Filling Performance as Function of Plating Thickness, Via Depth, and Current Density Compared with Conventional Product



Blind via diameter : 125 um



Via Filling Performance as Functions of Plating Thickness

Seed layer	Electroless copper			Void rate	
Dimple (um)	4.5	3.6	4.6	5.1	
15 um					0%
Dimple (um)	2.2	1.4	1.3	2.9	
20 um					0%
Dimple (um)	0.5	-2.9	-2.4	0.5	
25 um					0%

Blind via diameter : 125 um ; Dielectric : 75 um ; C.D. : 15 ASF



Bump Issue Compared with Conventional Product



Blind via diameter : 125 um ; Dielectric : 75 um ; C.D. : 15 ASF



Via Filling Performance as Functions of Current Density

Seed layer	Electroless copper			Void rate	
Dimple (um)	4.5	3.6	4.6	5.1	
15 ASF					0%
Dimple (um)	5.7	3.4	3.4	4.8	
20 ASF					0%

Blind via diameter : 125 um ; Dielectric : 75 um ; C.D. : 15 ASF



Result of Through Hole and Knee TP% Performance compared with Conventional Product

Through Hole TP% Performance

Knee TP% Performance





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Mass Production Status in Customer Site





Result of Reliability Test

Reliability Test				
Item	Method	Quality	Result	
Elongation & Tensile strength	Plating Thickness 2mil-4mil 25 samples	Elongation ≥15%	Pass	
		Tensile strength ≥248(N/mm²)	Pass	
IR Test	1.5m/min x 3cycles	Without current open	Pass	
Thermal shock	-50°C~125°C Qualification :100 cycles	Without current open	Pass	
Thermal Stress	288°C Solder immersion for 10 second Qualification :3 cycles	Without crack issue	Pass	



Summary

- Good surface appearance.
- Exceptional microvia filling performance (no bump/skip plating/void).
- Simultaneous microvia filling and through-hole plating at low surface thickness.
- Excellent deposit physical properties and interconnect reliability.
- > All bath additive components can be monitored by CVS.



Q & A



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Thank You

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